

**Amendments to the Specification:**

Please amend the specification as follows:

Please replace paragraphs [0001], [0002], and [0015] with the following rewritten paragraphs:

[0001] This application is related to U.S. Patent Application No. 10/016,710, entitled METHOD OF ENHANCING CLEAR FIELD PHASE SHIFT MASKS WITH CHROME BORDER AROUND PHASE 180 REGIONS; U.S. Patent Application No. 10/016,702, entitled METHOD OF ENHANCING CLEAR FIELD PHASE SHIFT MASKS BY ADDING PARALLEL LINE TO PHASE 0 REGION; U.S. Patent Application No. 10/016,273, entitled METHOD OF ENHANCING CLEAR FIELD PHASE SHIFT MASKS WITH BORDER REGIONS AROUND PHASE 0 AND PHASE 180 REGIONS; and U.S. Patent Application No. 10/016,441, entitled METHOD OF ENHANCING CLEAR FIELD PHASE SHIFT MASKS WITH BORDER AROUND OUTSIDE EDGES OF PHASE ZERO REGIONS, all of which are assigned to the same assignee as the present application.

[0002] This application is a continuation-in-part (CIP) application claiming priority under 35 U.S.C. 120 to U.S. Patent Application No. 09/772,577, filed January 30, 2001, entitled PHASE SHIFT MASK AND SYSTEM AND METHOD FOR MAKING THE SAME, by Todd Lukanc, one of the inventors of the present application.

[0015] An enhanced phase shift approach was developed to reduce the transition regions and move those regions away from the active edge to wider poly or corners of poly patterns where linewidth loss would have little or no impact. Examples of this enhanced phase shifting approach are described in U.S. Patent Application No. 09/772,577, entitled PHASE SHIFT MASK AND SYSTEM AND METHOD FOR MAKING SAME, filed on January 30, 2001, by Todd P. Lukanc (one of the inventors of the present application) and assigned to the assignee of the present application, incorporated herein by reference.